N-Channel Silicon MOSFET

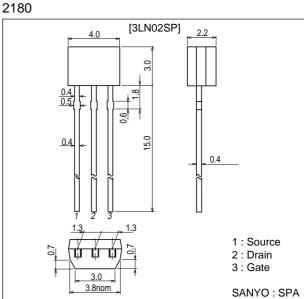


Features

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	۱D		0.3	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	1.2	А
Allowable Power Dissipation	PD		0.25	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			10	μA
Gate-to-Sourse Leakage Current	IGSS	VGS=±8V, VDS=0			±10	μA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =100µA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =150mA	0.4	0.56		S

Marking : YD

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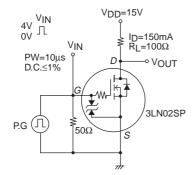
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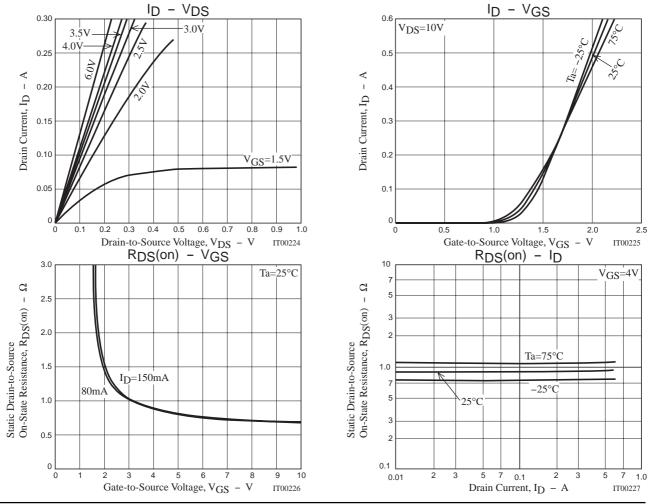
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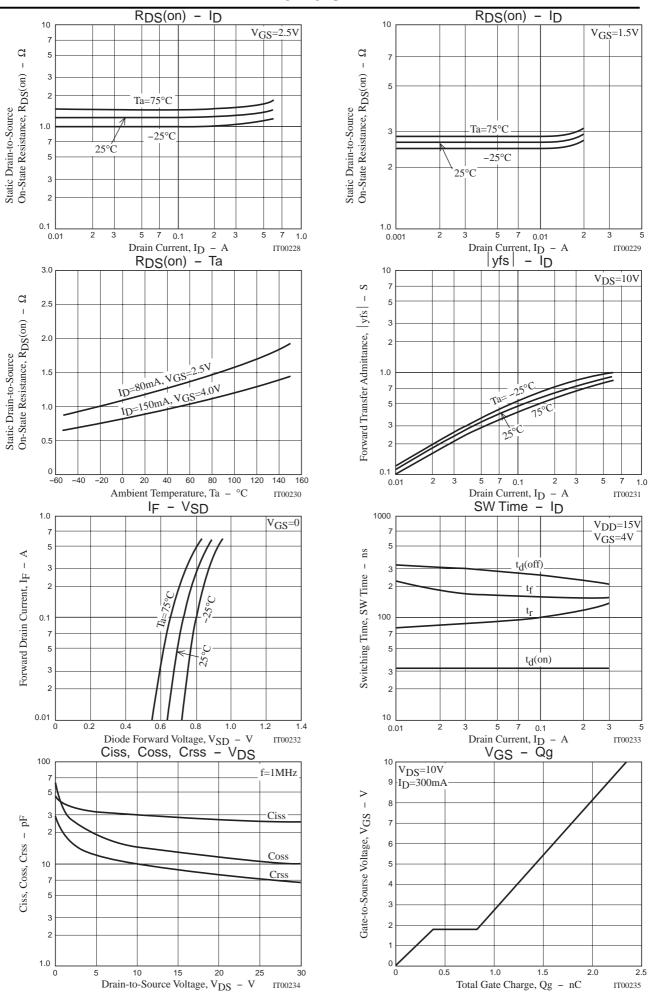
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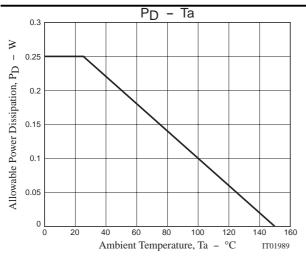
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Static Drain-to-Sourse on-State Resistance	R _{DS} (on)1	ID=150mA, VGS=4V		0.9	1.2	Ω
	R _{DS} (on)2	ID=80mA, VGS=2.5V		1.2	1.7	Ω
	RDS(on)3	ID=10mA, VGS=1.5V		2.6	5.2	Ω
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		30		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		10		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		32		ns
Rise Time	tr	See specified Test Circuit		110		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		250		ns
Fall Time	tf	See specified Test Circuit		160		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =300mA		2.34		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =300mA		0.38		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =300mA		0.45		nC
Diode Forward Voltage	VSD	IS=300mA, VGS=0		0.8	1.2	V

Switching Time Test Circuit









Note on usage: Since the 3LN02SP is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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